

Title (en)
HIGH-TEMPERATURE-RESISTANT COMPONENT STRUCTURE FREE OF SOLDERING AGENT, AND METHOD FOR ELECTRICAL CONTACT-
CONNECTION

Title (de)
HOCHTEMPERATURBESTÄNDIGE LÖTMITTELFREIE BAUELEMENTSTRUKTUR UND VERFAHREN ZUM ELEKTRISCHEN KONTAKTIEREN

Title (fr)
STRUCTURE DE COMPOSANT EXEMPT DE MÉTAL D'APPORT ET RÉSISTANT AUX HAUTES TEMPÉRATURES ET PROCÉDÉ DE MISE EN
CONTACT ÉLECTRIQUE

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Abstract (en)
[origin: WO2010072534A1] The invention relates to a component structure, comprising: an electrical or electronic component (10) having an upper contact area (12) on a top side of the component and a lower contact area (14) on an opposite underside of the component; an upper metal layer (40) and a lower metal layer (42); and an upper porous interlayer (20) and a lower porous interlayer (22). The upper interlayer mechanically and electrically conductively connects the upper metal layer to the upper contact area, and the lower interlayer mechanically and electrically conductively connects the lower metal layer to the lower contact area.

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Citation (search report)
See references of WO 2010072534A1

Citation (examination)
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• "CHAPTER 4: Eigenschaften und Charakterisierung von NTV-Verbindungen ED - MERTENS CHRISTIAN", 1 January 2004, DIE NIEDERTEMPERATUR-VERBINDUNGSTECHNIK DER LEISTUNGSELEKTRONIK (BOOK SERIES: FORTSCHRITT-BERICHTE VDI); [FORTSCHRITT-BERICHTE VDI : REIHE 21, ELEKTROTECHNIK ; 365], VDI VERLAG, DÜSSELDORF, GERMANY, PAGE(S) 73 - 115, ISBN: 978-3-18-336521-0, XP001526268

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